SEMICONDUCTOR

DATA SHEET

ABS2 THRU ABS10

Single Phase 1.0 AMP. Glass Passivated Bridge Rectifiers

Voltage Range 200 to 1000 Volts

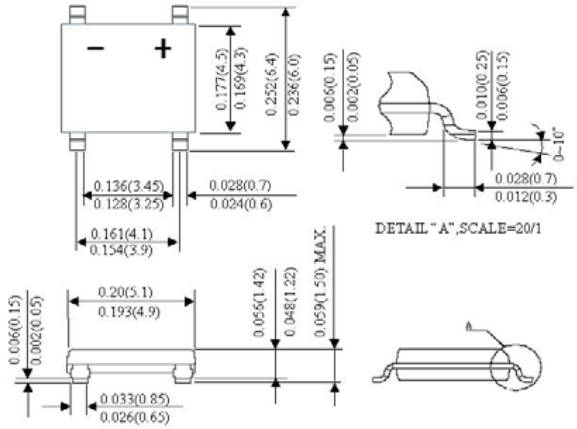
Current 1.0 Ampere

Thin Mini-Dip (THIN MD)



Features

- ✧ Glass passivated junction
- ✧ Ideal for printed circuit board
- ✧ Reliable low cost construction utilizing molded plastic technique
- ✧ High temperature soldering guaranteed: 260℃ / 10 seconds / 0.375" (9.5mm) lead length at 5 lbs., (2.3 kg) tension
- ✧ Small size, simple installation Leads solderable per MIL-STD-202, Method 208
- ✧ High surge current capability



Dimensions in inches and (millimeters)

Maximum Ratings and Electrical Characteristics

Rating at 25℃ ambient temperature unless otherwise specified.
Single phase, half wave, 60 Hz, resistive or inductive load.
For capacitive load, derate current by 20%

Type Number	Symbol	ABS2	ABS4	ABS6	ABS8	ABS10	Units
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	200	400	600	800	1000	V
Maximum RMS Voltage	V_{RMS}	140	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	200	400	600	800	1000	V
Maximum Average Forward Rectified Current On aluminum substrate	$I_{(AV)}$	1.0					A
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I_{FSM}	35					A
Maximum Instantaneous Forward Voltage @ 0.4A	V_F	0.95					V
Maximum DC Reverse Current @ T_A=25℃ at Rated DC Blocking Voltage	I_R	10					uA uA
Typical Thermal resistance Junction to Lead On aluminum substrate On Glass-Epoxy substrate	$R\theta_{JL}$ $R\theta_{JA}$	25 62.5 80					℃/W
Operating Temperature Range	T_J	-55 to +150					℃
Storage Temperature Range	T_{STG}	-55 to +150					℃
I2t Rating for fusing (t<8.3ms)	I2t	10.4					A2t

DEVICE CHARACTERISTICS

ABS2 THRU ABS10

RATINGS AND CHARACTERISTIC CURVES

FIG.1 MAXIMUM FORWARD CURRENT DERATING CURVE

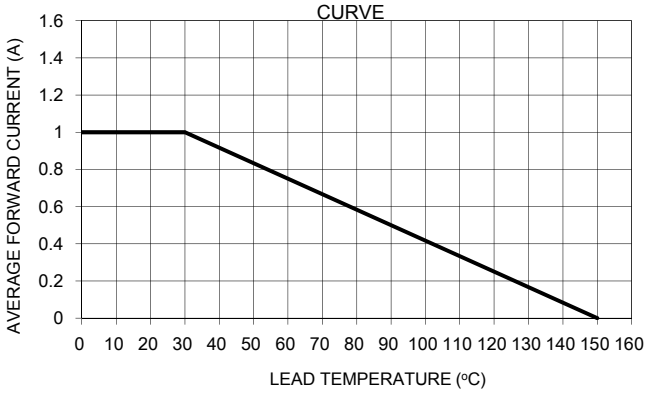


FIG. 2 TYPICAL REVERSE CHARACTERISTICS

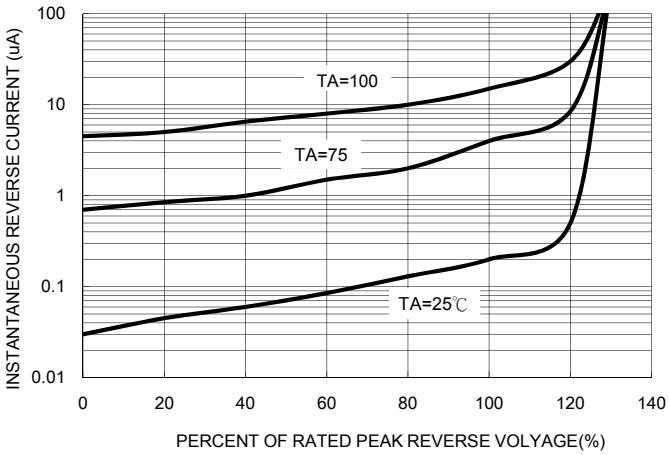


FIG. 3 MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

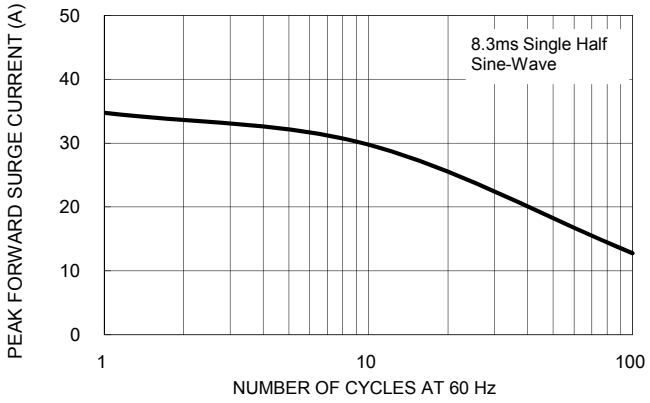


FIG. 4 TYPICAL JUNCTION CAPACITANCE

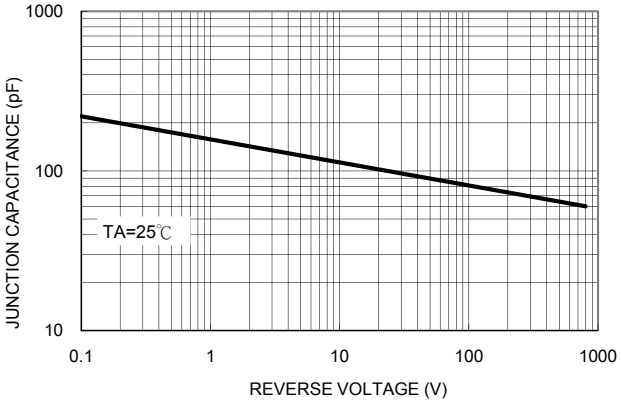


FIG. 5 TYPICAL FORWARD CHARACTERISTICS

